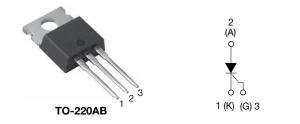


Vishay Semiconductors

FREE

Thyristor High Voltage, Phase Control SCR, 16 A



PRODUCT SUMMARY		
Package	TO-220AB	
Diode variation	Single SCR	
I _{T(AV)}	10 A	
V _{DRM} /V _{RRM}	800 V, 1200 V	
V _{TM}	1.4 V	
I _{GT}	60 mA	
TJ	- 40 °C to 125 °C	

FEATURES

- Designed and qualified according to JEDEC-JESD47
- 125 °C max. operating junction temperature
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>
 HALOGEN

APPLICATIONS

• Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-16TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operating up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS				
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS				
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	13.5	17	А	

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	10	۸		
I _{RMS}		16	A		
V _{DRM} /V _{RRM}	Range ⁽¹⁾	800/1200	V		
I _{TSM}		200	А		
V _T	10 A, T _J = 25 °C	1.4	V		
dV/dt		500	V/µs		
dl/dt		150	A/µs		
TJ	Range	- 40 to 125	°C		

Note

⁽¹⁾ For higher voltage up to 1600 V contact factory

VOLTAGE RATINGS							
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} ∕I _{DRM} AT 125 °C mA				
VS-16TTS08PbF, VS-16TTS08-M3	800	800	10				
VS-16TTS12PbF, VS-16TTS12-M3	1200	1200	10				

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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES		
FARAMETER			TEST CONDITIONS	TYP.	MAX.	UNITS	
Maximum average on-state current	I _{T(AV)}	T _C = 98 °C, 1	80° conduction, half sine wave	1			
Maximum RMS on-state current	I _{RMS}			1	6	Α	
Maximum peak, one-cycle,		10 ms sine p	ulse, rated V _{RRM} applied	17	70	A	
non-repetitive surge current	I _{TSM}	10 ms sine p	ulse, no voltage reapplied	20	00	1	
Maximum I ² t for fusing	l ² t	10 ms sine p	ulse, rated V _{RRM} applied	144		A ² s	
	1-1	10 ms sine p	200		A-5		
Maximum I ² √t for fusing	l²√t	t = 0.1 to 10 r	ns, no voltage reapplied	2000		A²√s	
Maximum on-state voltage drop	V_{TM}	10 A, T _J = 25	10 A, T _J = 25 °C			V	
On-state slope resistance	r _t	T 105 %O		r _t T _{.I} = 125 °C		l.0	mΩ
Threshold voltage	V _{T(TO)}	1j=125 0		1.1		V	
Maximum reverse and direct leakage current	1/1	T _J = 25 °C	V _R = Rated V _{RRM} /V _{DRM}	0.5			
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	VR = nated VRRM/ VDRM	10			
Holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A 16TTS08PbF, 16TTS12PbF, T_J = 25 °C		-	150	mA	
Maximum latching current	١ _L	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$		°C 200]	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$, linear to 80 °C, $V_{DRM} = R_g - k = Open$		en 500		V/µs	
Maximum rate of rise of turned-on current	dl/dt			150		A/µs	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	W	
Maximum average gate power	P _{G(AV)}		2.0	vv	
Maximum peak positive gate current	+ I _{GM}		1.5	А	
Maximum peak negative gate voltage	- V _{GM}		10	V	
	I _{GT}	Anode supply = 6 V, resistive load, T_J = - 65 °C	90	mA	
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T_J = 25 °C	60		
		Anode supply = 6 V, resistive load, T_J = 125 °C	35		
M		Anode supply = 6 V, resistive load, T_J = - 65 °C	3.0		
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$	2.0	V	
voltage to trigger		Anode supply = 6 V, resistive load, T_J = 125 °C	1.0	v	
Maximum DC gate voltage not to trigger	V _{GD}	$T = 125 \circ C M$ = Poted value	0.25		
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	2.0	mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9	
Typical reverse recovery time	t _{rr}	T _{.1} = 125 °C	4	μs
Typical turn-off time	tq	1J=125 C	110	

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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		- 40 to 125	°C
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	1.3	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	oz.
Mounting torque	minimum			6 (5)	kgf ⋅ cm
	maximum			12 (10)	(lbf ⋅ in)
Marking davias			Case style TO-220AB	16TTS08	
Marking device				16TTS12	

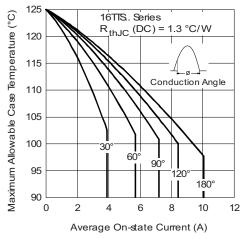
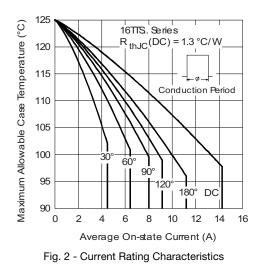


Fig. 1 - Current Rating Characteristics



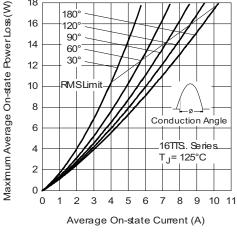


Fig. 3 - On-State Power Loss Characteristics

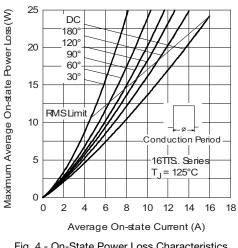


Fig. 4 - On-State Power Loss Characteristics

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VS-16TTS..PbF Series, VS-16TTS..-M3 Series

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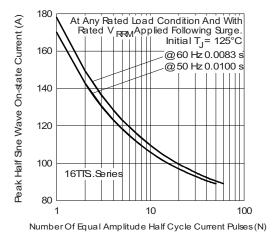


Fig. 5 - Maximum Non-Repetitive Surge Current

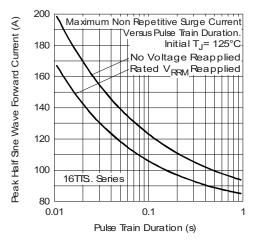


Fig. 6 - Maximum Non-Repetitive Surge Current

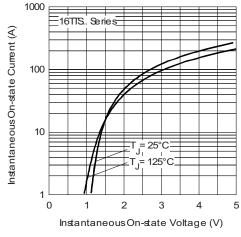


Fig. 7 - On-State Voltage Drop Characteristics

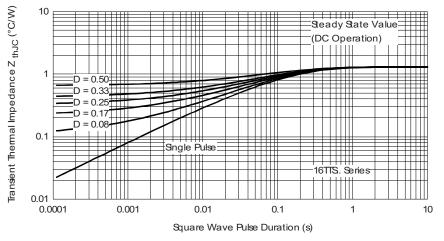


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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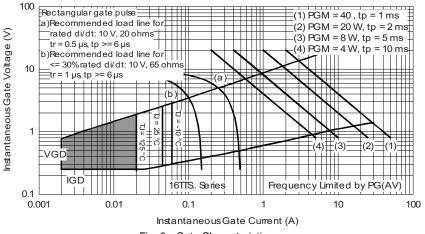


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	16	т	т	S	12	PbF
		(2)	(3)	4	(5)	6	(7)
	<u> </u>	\bigcirc		niconduc	0	duct	\bigcirc
	2 -		rent rati			duct	
	3 -			guration	1:		
	4 -		Single t kage:	hyristor			
	Ŀ		TO-220	AB			
	5 -	Тур	e of silic	on:			
	6 -			ter grade le x 100			08 = 80
	7 -			tal digit:			12 = 12
				(Pb)-fre			-
		-M3	= Halog	jen-free,	RoHS	complia	nt, and

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-16TTS08PbF	50	1000	Antistatic plastic tubes			
VS-16TTS08-M3	50	1000	Antistatic plastic tubes			
VS-16TTS12PbF	50	1000	Antistatic plastic tubes			
VS-16TTS12-M3	50	1000	Antistatic plastic tubes			

LINKS TO RELATED DOCUMENTS				
Dimensions		www.vishay.com/doc?95222		
Dort moreling information	TO-220AB PbF	www.vishay.com/doc?95225		
Part marking information	TO-220AB -M3	www.vishay.com/doc?95028		

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Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches





.ead	assignments

Diodes

1. - Anode/open 2. - Cathode 3. - Anode

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NUTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- ⁽³⁾ Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left(4\right) }$ Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. 10.51 0.414 10.11 0.398 3,6 Е E1 6.86 8.89 0.270 0.350 6 E2 0.76 0.030 7 --2.41 2.67 0.095 0.105 е 0.208 e1 4.88 5.28 0.192 H1 6.09 6.48 0.240 0.255 6,7 13.52 14.02 0.532 0.552 L L1 3.32 3.82 0.131 0.150 2 ØΡ 3.54 3.73 0.139 0.147 2.60 0.102 Q 3.00 0.118 90° to 93° 90° to 93° θ

Conforms to JEDEC outline TO-220AB

- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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